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LTspice ?

LTspice is a free circuit simulation program developed by Linear Technology, now a part of Analog Devices. It is widely used for power conversion, circuit, and power system design. It provides powerful features to help users model and analyze various types of circuits. Additionally, it is widely used among users, with many documents and resources available.





Installation

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LTspice Installation

- Search for LTspice on Google or click the link below

https://www.analog.com/en/lp/002/tools/ltspice-simulator-kr.html





LTspice Installation

- Download according to your OS version







♦ LTspice Installation

- Execute the downloaded file (LTspice64.msi)



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♦ LTspice Installation

- Search or click the icon on the desktop







LTspice Basics



♦ LTspice Basics

Click on File → New Schematic, an empty schematic window will pop-up.



New Schematic Window

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◆ LTspice Basics – Key shortcuts

Description	Shortcut
Configure Analysis	А
Run/Pause Simulation	Alt + R
Stop Simulation	Alt + S
Zoom to Fit	Space
Place Component	Р
Draw Wire	W
Place Ground	G
Place Voltage Source	V
Place Resistor	R
Place Capacitor	С
Place Inductor	L
Place Diode	D

Description	Shortcut
Place Net Name	Ν
Move Mode	М
Stretch Mode	S
Delete Mode	Del or Backspace
Duplicated Mode	Ctrl + C
Rotate	Ctrl + R
Mirror	Ctrl + E
Undo	Ctrl + Z
New Schematic	Ctrl + N
Save	Ctrl + S
SPICE Directive	



◆ LTspice Basics – Component Values (SI Unit)

K, k, kilo = 10^3	M , m, milli = 10^{-3}
MEG, meg = 10^6	U, u, micro = 10 ⁻⁶
G , g , giga = 10 ⁹	N, n, nano = 10 ⁻⁹
T, t, terra = 10 ¹²	P, p, pico = 10 ⁻¹²
	F , f , femto = 10^{-15}



LTspice Basics - NCSU 45nm CMOS Model Setup

In this semester, we will be using the NCSU 45nm CMOS Model.

The uploaded file (models_nom) contains the definitions of MOSFET's characteristics.

This is an open-source for 45nm CMOS technology node provided by North Carolina State University (NCSU).

NMOS_THKOX.inc	2007-08-10 오전 3:54	INC 파일
NMOS_VTG.inc	2010-02-19 오전 2:53	INC 파일
NMOS_VTH.inc	2010-02-16 오후 11:54	INC 파일
NMOS_VTL.inc	2010-02-19 오전 2:53	INC 파일
PMOS_THKOX.inc	2007-08-10 오전 3:54	INC 파일
PMOS_VTG.inc	2010-02-16 오후 11:54	INC 파일
PMOS_VTH.inc	2010-02-16 오후 11:54	INC 파일
PMOS_VTL.inc	2010-02-16 오후 11:54	INC 파일

models_nom

* Customized PTM	45 NMOS NMOS_VTH		
.model NMOS_VT	I nmos level = 54		
<pre>* parameters related to the technology node +tnom = 27 epsrox = 3.9 +eta0 = 0.008 nfactor = 1.6 wint = 5e-09 +cgso = 1.1e-010 cgdo = 1.1e-10</pre>			
* parameters cust +toxe = 1.63e-09 +dtox = 6.3e-10 +vth0 = 0.6078 k +rdsw = 155 nde	brized by the user toxp = 1.0e-09 to lint = 3.75e-09 1 = 0.4 u0 = 0.05 y p = 3.24e+018 xj = 1	xm = 1.63e-09 toxre vsat = 170000 .98e-08	ef = 1.63e-09
+version = 4.0 +capmod = 2	binunit = 1 igcmod = 1	paramchk= 1 igbmod = 1	mobmod = 0 geomod =
+diomod = 1 1	rdsmod = 0	rbodymod= 1	rgatemod=
+permod = 1	acnqsmod= 0	trngsmod= 0	

NMOS_VTL.inc



LTspice Basics - NCSU 45nm CMOS Model Setup



1) To apply the PDK, click the **Settings**

9 Settings ×	
Operation Schematic Waveforms SPICE Save Defaults	📒 LTsp
Netlist Options Compression Search Paths Internet Hacks	~
User libraries directory - libraries, symbols, plot.defs, user.*(.dio, etc)[*]	
C:#Users#user#Documents#LTspice Browse	⊕ 새로
Separate search path directories with semicolons or new lines.	수 홈
Symbol Search Path[*]	🗾 갤
	> 🌰 최태
	🛄 바
Library Search Path[*]	<u>↓</u> 다
	문·
	3) Ado
	- /
[*] Setting remembered between program invocations.	
Reset to Default Values	
확인 취소 도움말	

2) Search Paths → User libraries directory Check the existing library path



3) Add 'models_nom' folder to the library path

Finish !





Inverter Design Example



◆ Inverter Design Using a NCSU 45nm CMOS Model



Inverter Schematic



1) File \rightarrow New Schematic (Ctrl + N)



◆ Inverter Design Using a NCSU 45nm CMOS Model

We want to place components such as voltage sources, MOSFETs and GND.



2) Right-Click on background→ Draft → Component (P)



◆ Inverter Design Using a NCSU 45nm CMOS Model



3) There are a total of 4 MOSFETs. We will be using **nmos4** and **pmos4** among them.



♦ Inverter Design Using a NCSU 45nm CMOS Model

C:WUsersWuserWAppDataWLocalWLTspiceWlibWsym ✓ Search: Go to analog.com C:WUsersWuserWAppDataWLocalWLTspiceWlibWsymW MOC [ADC] bv ind2 plf [Comparators] cap 15016750-2 pmos [Comtrib] csw ISO7637-2 pmos [DAC] diode load pnp2 [DAC] diode load pnp2 [Digital] e load2 pnp4 [FilterProducts] ferriteBead mesfet res2 [Optons] FerriteBead2 nif schottky [PowerProducts] fra nmos4 SOAtherm-HeatSink [References] fraprobe nmos4 SOAtherm-HeatSink [Switches] g2 npn2 sw bi h npn3 tline bi2 ind npn4 TVSdiode		Top Directory:			
Search: Go to analog.com Image: Search: Go to analog.com Image: Search: Search: Image: Search: Go to analog.com Image: Search: Search: Image: Search: Search: <td></td> <td>C:\Users\user\A</td> <td>ppDataWLocalWLT</td> <td>spice₩lib₩sym</td> <td>~</td>		C:\Users\user\A	ppDataWLocalWLT	spice₩lib₩sym	~
Get Product Info Get Product Info		Search:		G	o to analog.com
[ADC] bv ind2 pjf [Comparators] cap ISO7637-2 pmos4 [CurrentMonitors] current LED pmp [DAC] diode load pnp2 [Digital] e load2 pnp4 [FilterProducts] e2 lpnp polcap [Misc] f Itline res [OpAmps] FerriteBead2 njf schottky [PowerProducts] fra nmos4 SOAtherm-HeatSink [References] fraprobe nmos4 SOAtherm-NMOS [Switches] g2 npn2 sw bi h npn3 tline bi2 ind npn4 TVSdiode		Image: C:₩Users₩user	#AppData₩Local#	LTspice₩lib₩sym₩	
Get Product Info		[ADC] [Comparators] [Contrib] [CurrentMonitors] [DAC] [Digital] [FilterProducts] [Misc] [Optos] [Optos] [PowerProducts] [References] [SpecialFunctions] [Switches] b] bi2	bv cap csw current diode e e2 f FerriteBead FerriteBead2 fra fraprobe g g2 h ind	ind2 ISO16750-2 ISO7637-2 LED load load2 lpnp ltline mesfet njf nmos nmos4 npn npn2 npn3 npn4	pif pmos pmos4 pmp pnp2 pnp4 polcap res res2 schottky SOAtherm-HeatSink SOAtherm-PCB sw tline TVSdiode
	Get Product Info	-			



In the case of PMOS, typically, a symbol with the drain terminal at the bottom is used.

However, in LTspice, the symbol has the Drain terminal at the top.

Nevertheless, since the drain and source of a MOSFET are symmetrical components,

there is no functional issue. It's just important to be aware that the names of

the source and drain may appear swapped in the simulation results.









◆ Inverter Design Using a NCSU 45nm CMOS Model



7) Right-Click and Draft \rightarrow SPICE Directive (.)

📁 Edit Text on the Schema	tic:		×
How to netlist this text	Justification	Font Size	ОК
CommentSPICE directive	Left ~ Vertical Text	1.5(default) ~	Cancel
.inc models_nom₩NMOS_VT	L.inc		•
Press Shift+Enter to start a ne	w line.		
0)			





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◆ Inverter Design Using a NCSU 45nm CMOS Model



 9) Right-Click on MOSFET instance (symbol) and change the model name to PMOS_VTL and NMOS_VTL
 Set the length (≥ 45nm) and width values to what you desire



10) Right-Click on **voltage source name** and change the instance name to vin

Right-Click on **voltage source instance (symbol)** and change the DC value

* nominal voltage of this PDK is 1V, so VDD \Rightarrow 1V



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◆ Inverter Design Using a NCSU 45nm CMOS Model



11) Label Net (N) \rightarrow **labeling IN** and **OUT**



Simulation



◆ 1. DC Operating Point Simulation

DC operating point simulation is used for checking each node's Voltage, Current.

Capacitors are treated as open circuits, while inductors are treated as short circuits.











◆ 1. DC Operating Point Simulation



- 6) After running the simulation, you can check the results in two ways.
 - 1. Directly probe nodes.
 - 2. Check the data in the results window.





♦ 2. DC sweep simulation

DC sweep simulation is used for seeing specific point's voltage or current variation when changing DC value





◆ 2. DC sweep simulation



2) DC sweep \rightarrow set up the simulation environment







♦ 3. Parametric Simulation

Parametric Simulation is an option with which you can view simulation results for varying values of specific parameter.



Parametric Simulation can be used for not only DC sweep but also AC sweep and Transient simulation.





♦ 3. Parametric Simulation

😕 LTspice - [Draft2.asc]				
File Edit Hierarchy View Simulate Tools Window Help				
The second se			D Monolithic MOSFET - M1	×
			Model Name: NMOS_VTL	ОК
 Click the Configure Analysis (A) 			Length(L): 45n	Cancel
1 Configure Applyin	(Width(W): {width_nmos}	
			Drain Area(AD):	
Transient AC Analysis DC sweep Noise DC Transfer DC op pnt Transient Frequency Response		0.5	Source Area(AS):	
Compute the DC operating point of a circuit while stepping independent sources and treating capacitances as open circuits and inductances as short circuits.	7	\downarrow \downarrow	Drain Perimeter(PD):	
1st Source 2nd Source 3rd Source			Source Perimeter(PS):	
Name of 1st source to sweep: vin		.op	No. Parallel Devices(M):	
Type of sweep: Linear V		.dc vin 0 1 0.01	NMOS VTL 1-45p w=(width pmos)	
Start value: 0			Width_11105	
Stop value: 1				
Increment: 0.01				
Syntax: .dc [<oct,dec,lin>] <source1> <start> <stop> [<incr>] [<source2>]</source2></incr></stop></start></source1></oct,dec,lin>	3)	Assign a parameter name	to the desired value for	or the sweep
.dc vin 0 1 0.01		(in this example, the width of	f the NMOS)	

2) Choose simulation type you want to view

ОК

Cancel

format : {parameter name}



♦ 3. Parametric Simulation



4) Enter the command using directives functions.SPICE Directive (.)

The simulation option displayed in black text will be run.

If you want to change the simulation, **right click on text** and click OK.

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♦ 3. Parametric Simulation



The simulation results correspond to six values for nmos_width ranging from 0.5u to 1u in increments of 0.1u

If you want to see current, click on the terminal of instance in schematic



♦ 4. AC Simulation

AC sweep is used for seeing **frequency response** at a specific node.

(Do Not confuse it; it is not used for time-domain simulation)









1) Right click on voltage source



2) DC Value is what you desire.

Make sure that Magnitude of AC Amplitude is set to 1







4) Select AC Analysis and Configure the simulation settings.



♦ 4. AC Simulation





7) This moment, I just want to see Magnitude

so right click on the right axis and click the 'Don't plot phase' button.





- 8) I want to check Gain and 3dB Bandwidth.
 - right click on background and 'Place Cursor on Active Trace' or C
- 9) To add the Cursor Position, right click on background and

'Note & Annotations \rightarrow Cursor Position' or L



♦ 4. AC Simulation





♦ 5. Transient Simulation

Transient simulation is used for time-domain responses at a specific node.





♦ 5. Transient Simulation



1) Right click on voltage source



2) Use any input you want to put in.

If you want to input sine wave, use SINE Functions.





♦ 5. Transient Simulation





4) Select Transient and setup stop time you want to see

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♦ 5. Transient Simulation







♦ 5. Transient Simulation





◆ 5. Transient Simulation



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- 3) Determine ro for the transistor at Vgs=0.6V
- 4) Run transient simulation and AC analysis simulation. Find DC gain and 3dB-bandwidth.





- 1. Follow the instructions
- 1-1) Draw CS Amp schematic



VIN(V1) voltage source setting

VDD(V2) voltage source setting



1-2) Run Transient and AC analysis simulation





Simulation result

Check input & output amplitude and CS Amp gain





1-2) Run Transient and AC analysis simulation



Check DC gain & 3dB Bandwidth





1-3) Find gm(transconductance) using DC sweep simulation



Drain current depending on V_{GS}





1-3) Find gm(transconductance) using DC sweep simulation

toolbar \rightarrow Plot Setting \rightarrow Add Trace \rightarrow Expression to add function (D(Id(M1)))

🍠 Add Traces to Plot	:	×
Available data:	Only list traces matching OK Asterisks match colons Cancel]
V(alable data) V(m 1#dbody) V(m 1#sbody) V(vd) V(vd) V(vin) I(R1) I(V1) I(V1) I(V2) Ib(M1) Ig(M1) Is(M1) v1		
Expression(s) to add:		
D(ld(M1))]
🗹 Auto Range	Id(M1): M1 transistor drain current	
	Add Trace	

D function calculates derivative of y in terms of x-axis' variable



gm and Drain current depending on V_{GS}





1-4) Find ro for transistor at $V_{GS} = 0.6V$ using DC sweep simulation







1-4) Find ro for transistor at $V_{GS} = 0.6V$ using DC sweep simulation



ro depending on V_{DS}



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